

FMS

1N60/1N60P

Schottky Barrier Diode

Features

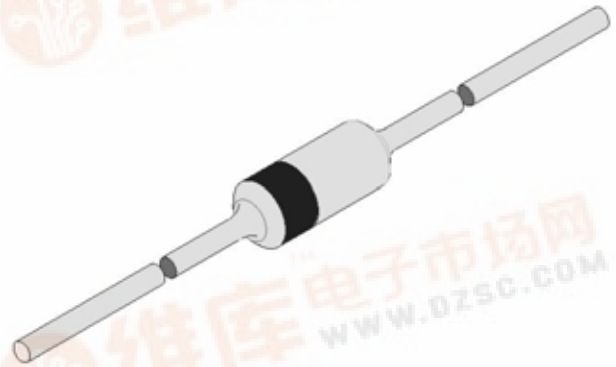
1. High reliability
2. Low reverse current and low forward voltage

Applications

Low current rectification and high speed switching

Construction

Silicon epitaxial planar



Absolute Maximum Ratings

$T_j=25$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage		1N60	V_{RRM}	40	V
		1N60P	V_{RRM}	45	V
Peak forward surge current	$t_p \leq 1 \text{ s}$	1N60	I_{FSM}	150	mA
		1N60P	I_{FSM}	500	mA
Forward continuous current	$T_a=25$	1N60	I_F	30	mA
		1N60P	I_F	50	mA
Storage temperature range			T_{stg}	-65~+125	

Maximum Thermal Resistance

$T_j=25$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on PC board 50mm x 50mm x 1.6mm	R_{thJA}	250	K/W

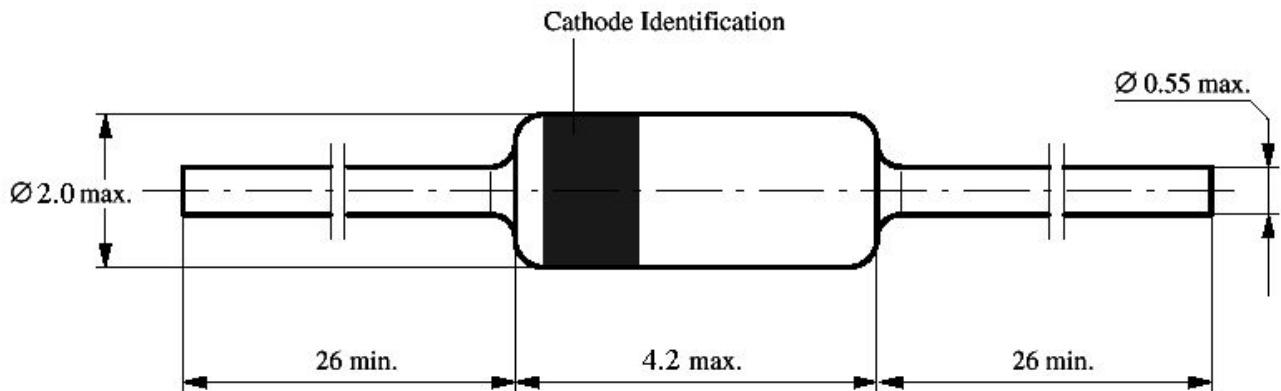


Electrical Characteristics

$T_j=25$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=1\text{mA}$	1N60	V_F		0.32	0.5	V
		1N60P	V_F		0.24	0.5	V
	$I_F=30\text{mA}$	1N60	V_F		0.65	1.0	V
		1N60P	V_F		0.65	1.0	V
Reverse current	$V_R=15\text{V}$	1N60	I_R		0.1	0.5	μA
		1N60P	I_R		0.5	1.0	μA
Junction capacitance	$V_R=1\text{V}, f=1\text{MHz}$	1N60	C_J		2.0		pF
	$V_R=10\text{V}, f=1\text{MHz}$	1N60P	C_J		6.0		pF
Reverse recovery time	$I_F=I_R=1\text{mA}, I_{tr}=1\text{mA}, R_C=100\Omega$		t_{rr}			1.0	ns

Dimensions in mm



Standard Glass Case
JEDEC DO 35

